

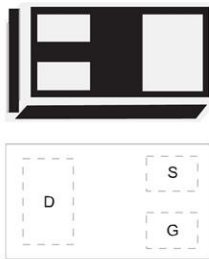
**Features**

- Surface Mount Package
- N-Channel Switch with Low  $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive
- ESD Protected
- - Complementary to TPM2009EP3

**Application**

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

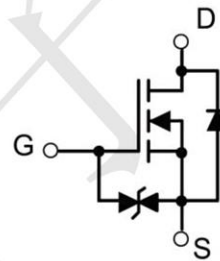
**Package and Pin Configuration**



**DFN1006-3L**

**Marking: N5.Ω**

**Circuit diagram**



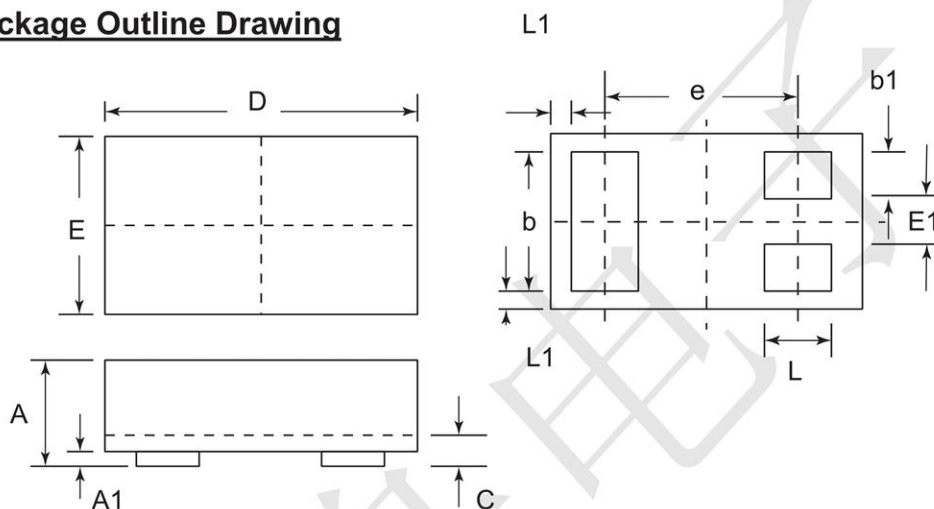
**Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$  unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 10$	V
Continuous Drain Current	$I_D$	0.7	A
Pulsed Drain Current ( $t=300\mu\text{s}$ ) <sup>(1)</sup>	$I_{DM}$	1.8	A
Power Dissipation <sup>(2)</sup>	$P_D$	100	mW
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

**Electrical Characteristics (  $T_A = 25^\circ\text{C}$  unless otherwise noted )**

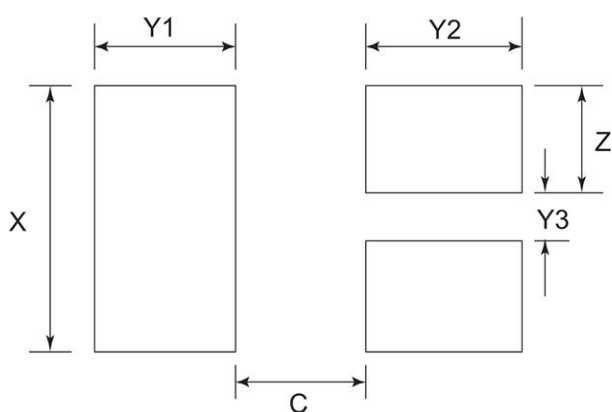
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$			1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 10V, V_{DS} = 0V$			$\pm 10$	$\mu A$
Gate threshold voltage <sup>(3)</sup>	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.35	0.75	1.1	V
Drain-source on-resistance <sup>(3)</sup>	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 650mA$		130	250	m $\Omega$
		$V_{GS} = 2.5V, I_D = 550mA$		190	370	
Forward transconductance	$g_{FS}$	$V_{DS} = 10V, I_D = 500mA$			1.2	S
<b>Dynamic characteristics<sup>(4)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 16V, V_{GS} = 0V, f = 1MHz$			120	pF
Output Capacitance	$C_{oss}$				20	
Reverse Transfer Capacitance	$C_{rss}$				15	
<b>Switching Characteristics<sup>(4)</sup></b>						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 500mA,$ $V_{GS} = 4.5V, R_G = 10\Omega$		6.7		ns
Turn-on rise time	$t_r$			4.8		
Turn-off delay time	$t_{d(off)}$			17.3		
Turn-off fall time	$t_f$			7.4		
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage <sup>(3)</sup>	$V_{DS}$	$I_S = 0.15A, V_{GS} = 0V$			1.2	V

**DFN1006-3L Package Outline Drawing**



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
b1	0.10	0.15	0.20	0.004	0.006	0.008
C	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
E1	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05 REF			0.0002 REF		

**Suggested Land Pattern**



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.25	0.010
X	0.65	0.024
Y1	0.50	0.020
Y2	0.50	0.020
Y3	0.25	0.010
Z	0.20	0.008

单击下面可查看定价，库存，交付和生命周期等信息

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